Abstracts

26 GHz Coplanar SiGe MMICs

C. Rheinfelder, K. Strohm, F. Beisswanger, J. Gerdes, F.J. Schmuckle, J.F. Luy and W. Heinrich. "26 GHz Coplanar SiGe MMICs." 1996 MTT-S International Microwave Symposium Digest 96.1 (1996 Vol. I [MWSYM]): 273-276.

First results on coplanar MMICs with SiGe HBTs are presented. The circuits are fabricated on high-resistivity Si substrates using a double-mesa HBT process. In the Ka-band, an oscillator output power of 1 dBm and 4.4 dB gain for a one-stage amplifier are achieved. This demonstrates the potential of SiGe transistors for applications in the higher microwave range.

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